ADE-208-302(Z)

1SS286
Silicon Schottky Barrier Diode for Various Detector,High Speed Switching

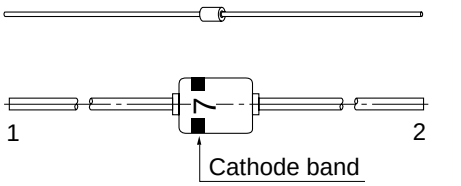
HITACHI

Rev. 0
Dec. 1994

Features

- Very low reverse current.
- Detection efficiency is very good.
- Small glass package (MHD) enables easy mounting and high reliability.

Outline



1. Cathode
2. Anode

Ordering Information

Type No.	Cathode band	Mark	Package Code
1SS286	Green	7	MHD

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	25	V
Forward current	I_F	35	mA
Power dissipation	P_d	150	mW
Lead temperature	T_l*	260	°C
Junction temperature	T_j	100	°C
Storage temperature	T_{stg}	-55 to +100	°C

* Value at distance 0.8mm from body for 10s max

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.6	V	I_F = 10 mA
Reverse voltage	V_R	25	—	—	V	I_R = 10 µA
Reverse current	I_R	—	—	10	nA	V_R= 10 V
Capacitance	C	—	—	1.2	pF	V_R = 0 V, f = 1 MHz
Capacitance deviation	ΔC	—	—	0.1	pF	V_R = 0 V, f = 1 MHz
Forward voltage deviation	ΔV_F	—	—	10	mV	I_F = 10 mA
ESD-Capability	—	10	—	—	V	*C=200pF , Both forward and reverse direction 1 pulse.

* Failure criterion ; $I_R \geq 20\mu A$
** Each group shall unify a multiple of 4 diodes

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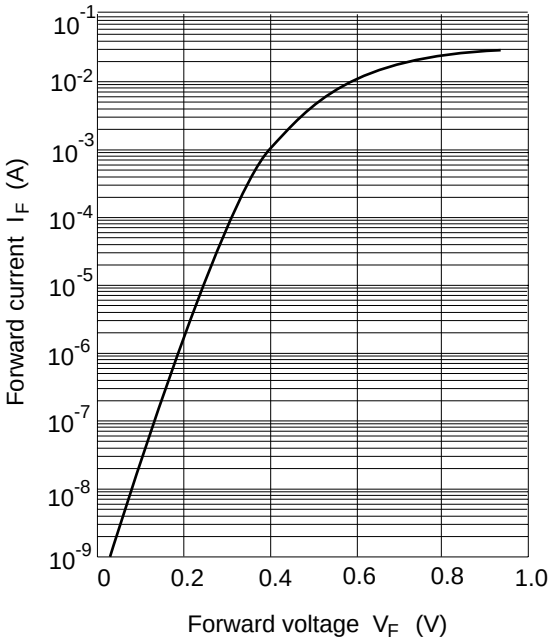


Fig.1 Forward current Vs. Forward voltage

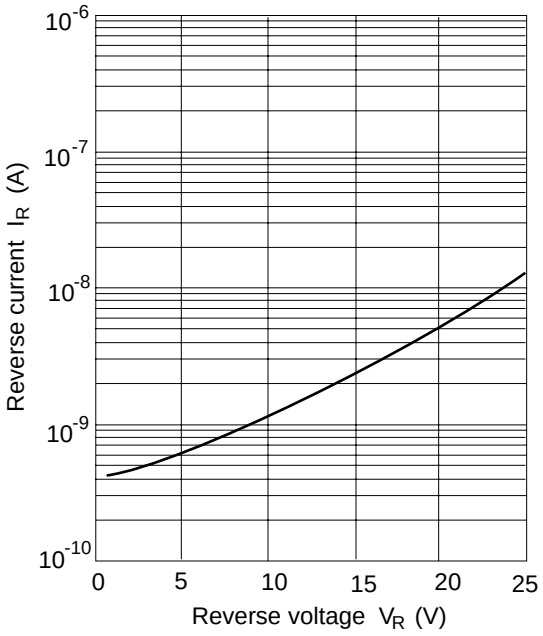


Fig.2 Reverse current Vs. Reverse voltage

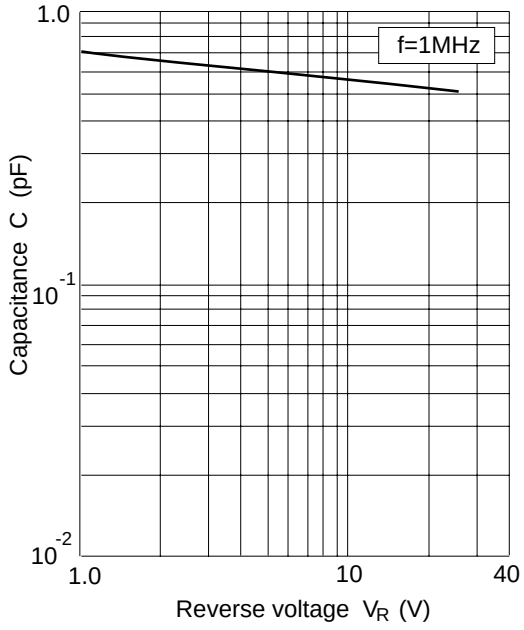
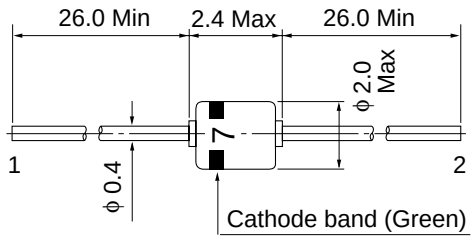


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



1 Cathode
2 Anode

HITACHI Code	MHD
JEDEC Code	DO-34
EIAJ Code	—
Weight (g)	0.084